#### SURFACE MOUNT SCHOTTKY BARRIER DIODES

#### **Features**

- Low switching losses
- Fast recovery time
- · Guard ring protected
- Hermetically sealed glass SMD package.

# 0.3 0.3

Cathode Mark

Plastic case MiniMELF Dimensions in mm

#### **APPLICATIONS**

- Low power, swiched-mode power supplies
- Rectifying
- Polarity protection

**Absolute Maximum Ratings and Characteristics** (Ratings at T<sub>amb</sub> = 25 °C unless otherwise specified.)

Absolute Maximum Ratings and Characteristics	(Tatings at	Tamb - 23 C diffess offici wise specified.)			
Parameter	Symbols	LM5817	LM5818	LM5819	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	V
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	24	36	48	V
Continuous Reverse Voltage	$V_R$	20	30	40	V
Crest Working Reverse Voltage	$V_{RWM}$	20	30	40	V
Average Forward Current (T <sub>amb</sub> = 60 °C)	I <sub>(AV)</sub>	1			Α
Non-repetitive Peak Forward Current $t = 10$ ms half sine wave; $T_j = T_{jmax}$ prior to surge: $V_R = 0$	I <sub>FSM</sub>	25			А
Forward Voltage $ \begin{array}{c} \text{at } I_F = 0.1 \text{ A} \\ \text{at } I_F = 1 \text{ A} \\ \text{at } I_F = 3 \text{ A} \end{array} $	V <sub>F</sub>	0.32 0.45 0.75	0.33 0.55 0.875	0.34 0.6 0.9	V
Reverse Current at $V_R = V_{RRMmax}^{1}$ at $V_R = V_{RRMmax} T_j = 100 ^{\circ}\text{C}$	I <sub>R</sub>		1 10		mA
Thermal Resistance	$R_{ heta JA} \ R_{ heta JL}$	150 60			K/W
Typical Diode Capacitance at V <sub>R</sub> = 4 V, f = 1 MHz	C <sub>D</sub>	70	50	50	pF
Junction Temperature	T <sub>J</sub>	125			°C
Storage Temperature Range	Ts	-65 to +175			°C
1)					<u> </u>

<sup>&</sup>lt;sup>1)</sup> Pulse test:  $tp = 300 \mu s$ ;  $\delta = 0.02$ 

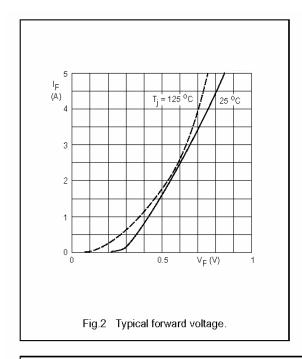


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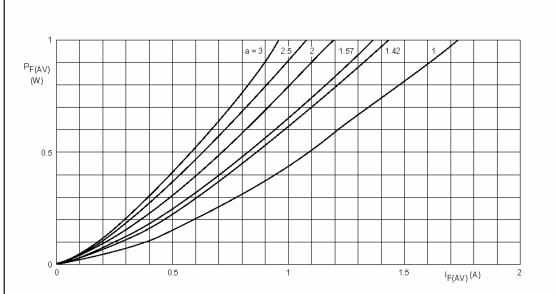


Fig.3 LM5817 Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(RMS)}/I_{F(AV)}$ .



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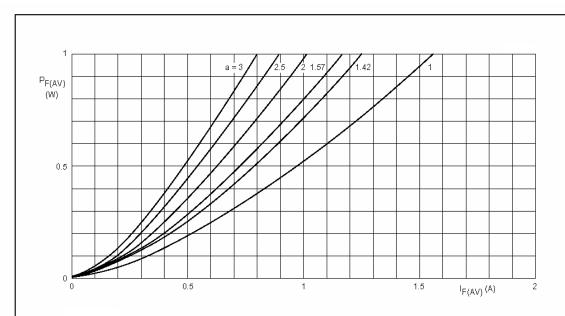


Fig.4 LM5818 Maximum values steady state forward power dissipation as a function of the average forward current; a = I<sub>F(RMS)</sub>/I<sub>F(AV)</sub>.

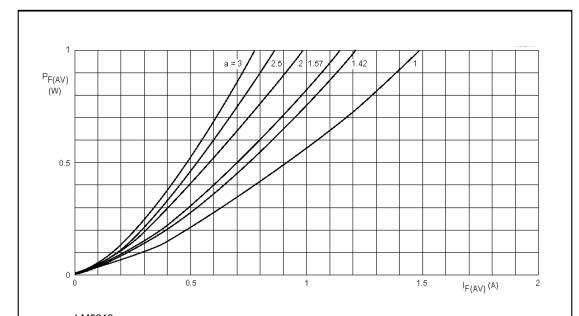


Fig.5 LM5819 Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(RMS)}/I_{F(AV)}$ .







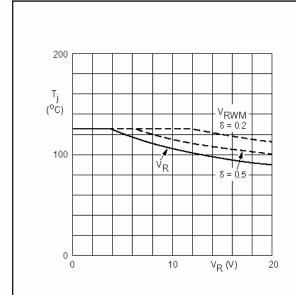


Fig.6 LM5817 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

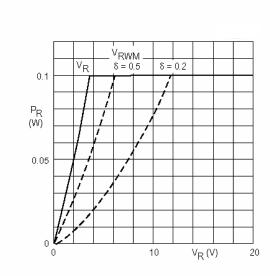


Fig.7 LM5817 Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

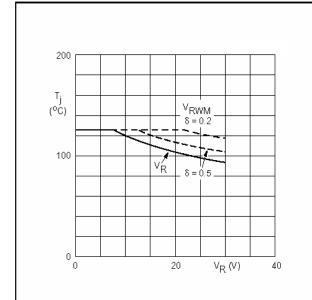


Fig.8 LM5818 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

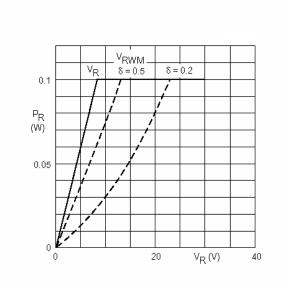


Fig.9 LM5818 3. Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.



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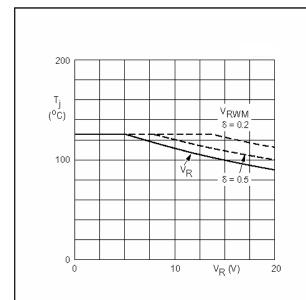
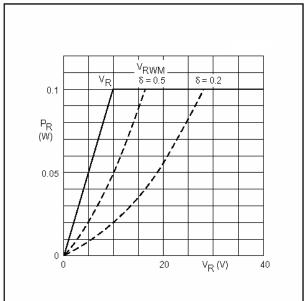


Fig.10 LM5819 Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.



LM5819 Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.



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